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BC490

High Current Transistors

PNP Silicon

Features

• This is a Pb-Free Device*



Rating	Symbol Value		Unit	
Collector – Emitter Voltage	V _{CEO}	-80	Vdc	
Collector – Base Voltage	V _{CBO}	-80	Vdc	
Emitter – Base Voltage	V _{EBO}	-4.0	Vdc	
Collector Current – Continuous	Ic	-1.0	Adc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C	

THERMAL CHARACTERISTICS

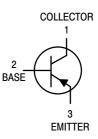
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

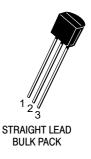


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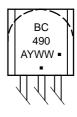
http://onsemi.com



TO-92 CASE 29 STYLE 17



MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

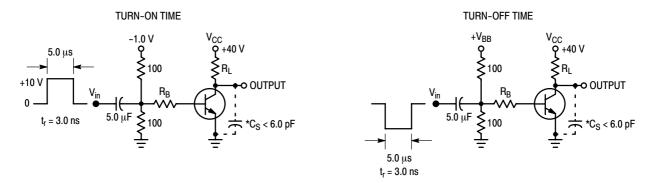
Device	Package	Shipping
BC490G	TO-92 (Pb-Free)	5000 Units / Bulk

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

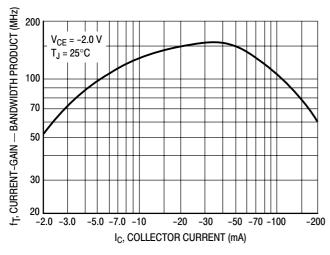
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		1		<u> </u>	-1
Collector – Emitter Breakdown Voltage (Note 1) (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-80	_	_	Vdc
Collector – Base Breakdown Voltage ($I_C = -100 \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	-80	_	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-4.0	_	-	Vdc
Collector Cutoff Current (V _{CB} = -60 Vdc, I _E = 0)	I _{CBO}	_	_	-100	nAdc
ON CHARACTERISTICS	<u> </u>				
DC Current Gain $ \begin{array}{l} (I_C = -10 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ (I_C = -100 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ (I_C = -1.0 \text{ Adc}, V_{CE} = -5.0 \text{ Vdc}) \end{array} $	h _{FE}	40 60 15	_ _ _	- 400 -	_
Collector – Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$) ($I_C = -1.0 \text{ Adc}$, $I_B = -100 \text{ mAdc}$)	V _{CE(sat)}	- -	-0.25 -0.5	-0.5 -	Vdc
Base – Emitter Saturation Voltage ($I_C = -500$ mAdc, $I_B = -50$ mAdc) ($I_C = -1.0$ Adc, $I_B = -100$ mAdc)	V _{BE(sat)}	- -	-0.9 -1.0	-1.2 -	Vdc
DYNAMIC CHARACTERISTICS			•		
Current–Gain – Bandwidth Product (I _C = -50 mAdc, V _{CE} = -2.0 Vdc, f = 100 MHz)	f _T	_	150	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	9.0	-	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ib}	_	110	_	pF

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle 2%.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



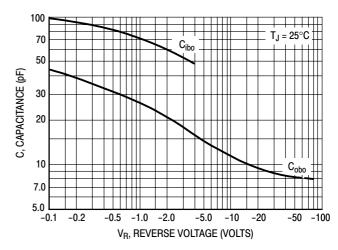


Figure 2. Current-Gain — Bandwidth Product

Figure 3. Capacitance

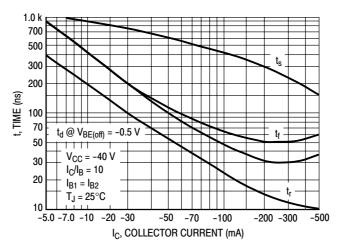


Figure 4. Switching Time

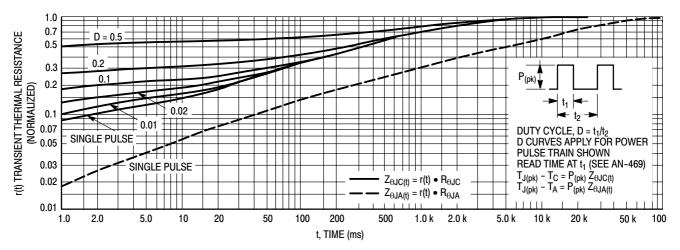


Figure 5. Thermal Response

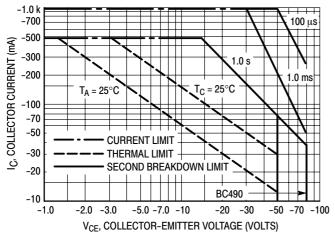


Figure 6. Active Region, Safe Operating Area

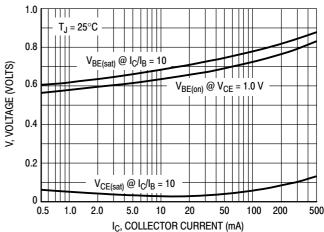


Figure 7. "On" Voltages

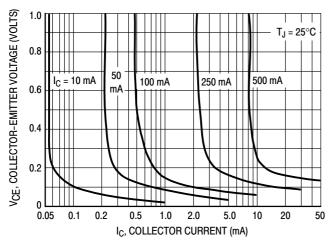


Figure 8. Collector Saturation Region

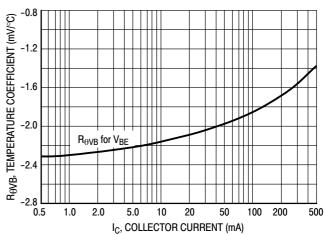


Figure 9. Base-Emitter Temperature Coefficient

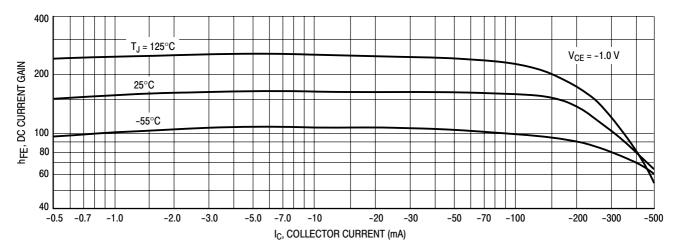
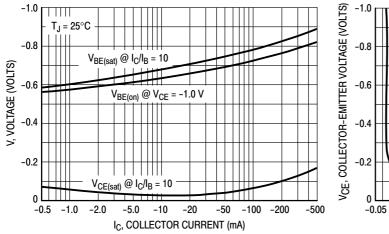


Figure 10. DC Current Gain



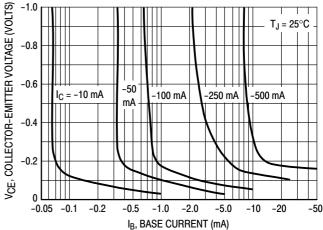


Figure 11. "On" Voltages

Figure 12. Collector Saturation Region

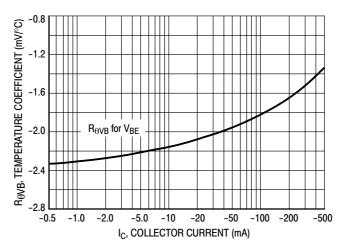
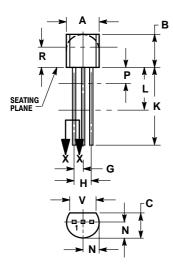


Figure 13. Base-Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



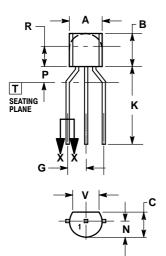
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17:

COLLECTOR PIN 1.

BASE

EMITTER

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